



## AO4902

### Dual N-Channel Enhancement Mode Field Effect Transistor with Schottky Diode

#### General Description

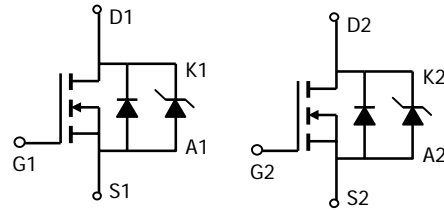
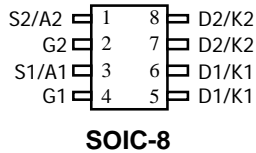
The AO4902 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The two identical MOSFETs are co-packaged in parallel with a Schottky diode, making them ideal for many bridge and totem pole applications, for e.g. DDR memory. *Standard Product AO4902 is Pb-free (meets ROHS & Sony 259 specifications). AO4902L is a Green Product ordering option. AO4902 and AO4902L are electrically identical.*

#### Features

$V_{DS}$  (V) = 30V  
 $I_D$  = 6.9A ( $V_{GS}$  = 10V)  
 $R_{DS(ON)} < 27m\Omega$  ( $V_{GS}$  = 10V)  
 $R_{DS(ON)} < 32m\Omega$  ( $V_{GS}$  = 4.5V)  
 $R_{DS(ON)} < 50m\Omega$  ( $V_{GS}$  = 2.5V)

#### SCHOTTKY

$V_{DS}$  (V) = 30V,  $I_F$  = 3A,  $V_F$  = 0.5V@1A



#### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	$V_{DS}$	30		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	6.9	A
		$T_A=70^\circ\text{C}$	5.8	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	40		
Schottky reverse voltage	$V_{KA}$		30	V
Continuous Forward Current <sup>A</sup>	$I_F$	$T_A=25^\circ\text{C}$	3	A
		$T_A=70^\circ\text{C}$	2	
Pulsed Forward Current <sup>B</sup>	$I_{FM}$		40	
Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	2	W
		$T_A=70^\circ\text{C}$	1.44	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ\text{C}$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State		74	110	
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	35	40	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	47.5	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State		71	110	
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	32	40	

**Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.7	1	1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	25			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=6.9\text{A}$ $T_J=125^\circ\text{C}$		22.6 33	27 40	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=6.0\text{A}$		27	32	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=5\text{A}$		42	50	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=5\text{A}$	12	16		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$		0.71	1	V
$I_S$	Maximum Body-Diode Continuous Current				3	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		846	1050	pF
$C_{oss}$	Output Capacitance			96		pF
$C_{rss}$	Reverse Transfer Capacitance			67		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.24	3.6	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=6.9\text{A}$		9.6	12	nC
$Q_{gs}$	Gate Source Charge			1.65		nC
$Q_{gd}$	Gate Drain Charge			3		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=2.2\Omega$ , $R_{GEN}=3\Omega$		3.2	4.8	ns
$t_r$	Turn-On Rise Time			4.5	6.8	ns
$t_{D(off)}$	Turn-Off DelayTime			26.3	40	ns
$t_f$	Turn-Off Fall Time			4.8	7	ns
$t_{rr}$	Body Diode Reverse Recovery time	$I_F=5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		15.5	20	ns
$Q_{rr}$	Body Diode Reverse Recovery charge	$I_F=5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		7.9		nC
<b>SCHOTTKY PARAMETERS</b>						
$V_F$	Forward Voltage Drop	$I_F=1.0\text{A}$		0.45	0.5	V
$I_{rm}$	Maximum reverse leakage current	$V_R=30\text{V}$		0.007	0.05	mA
		$V_R=30\text{V}$ , $T_J=125^\circ\text{C}$		3.2	10	
		$V_R=30\text{V}$ , $T_J=150^\circ\text{C}$		12	20	
$C_T$	Junction Capacitance	$V_R=15\text{V}$		37		pF

A: The value of  $R_{\theta JA}$  is measured with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using  $80\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

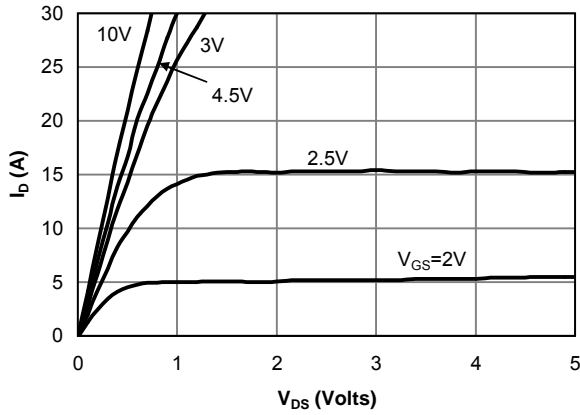


Fig 1: On-Region Characteristics

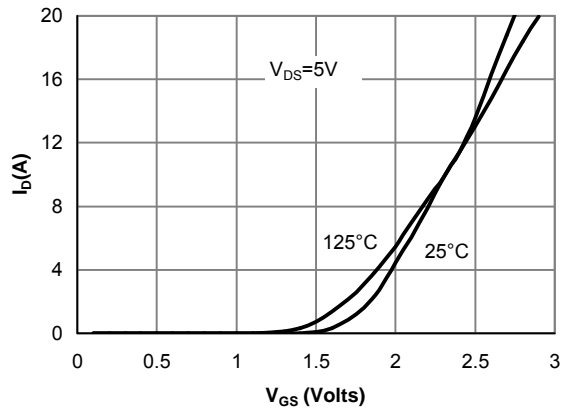


Figure 2: Transfer Characteristics

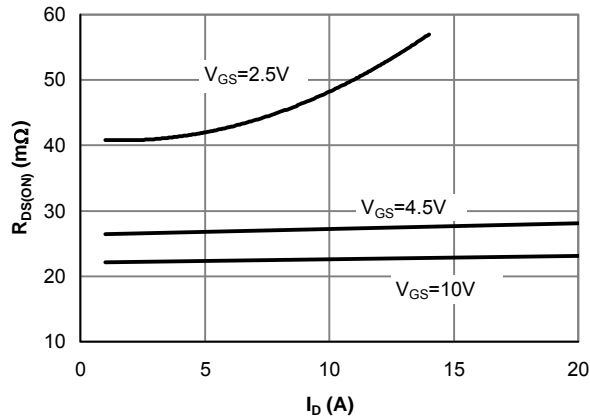


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

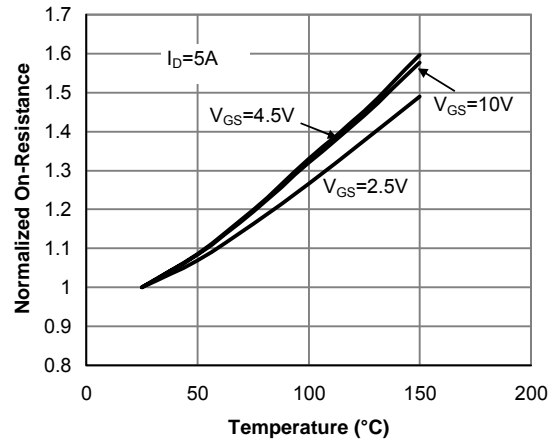


Figure 4: On resistance vs. Junction Temperature

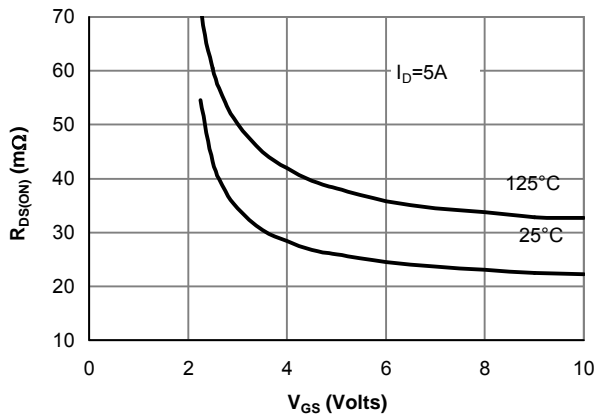


Figure 5: On resistance vs. Gate-Source Voltage

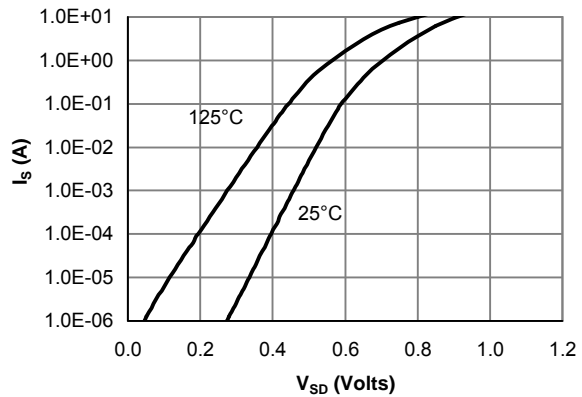


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

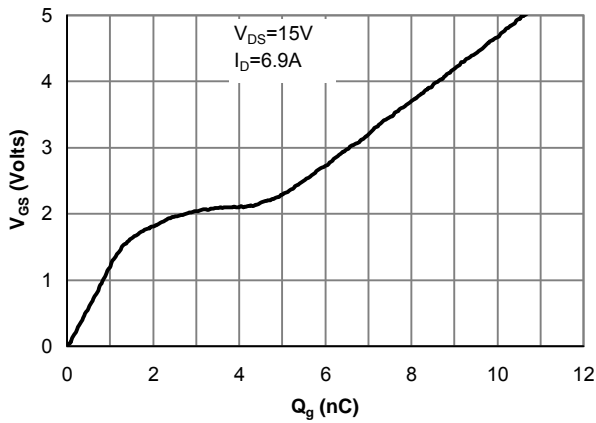


Figure 7: Gate-Charge Characteristics

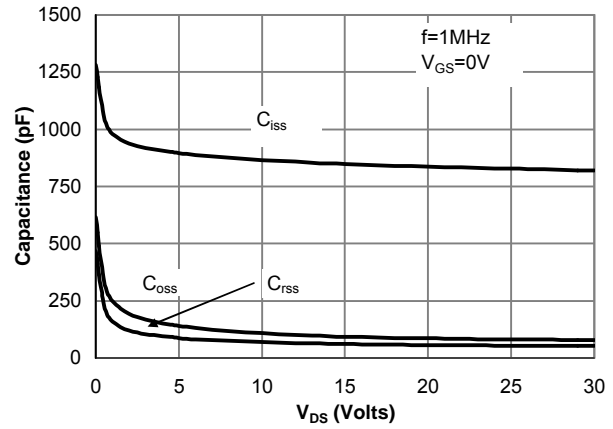


Figure 8: Capacitance Characteristics

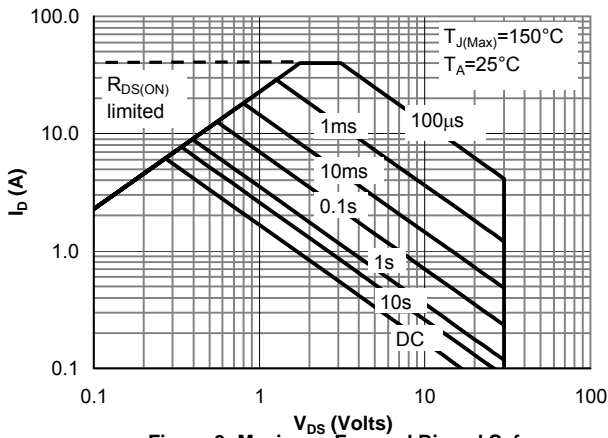


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

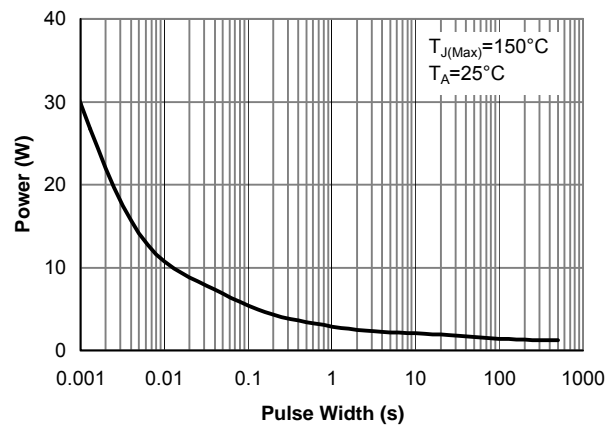


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

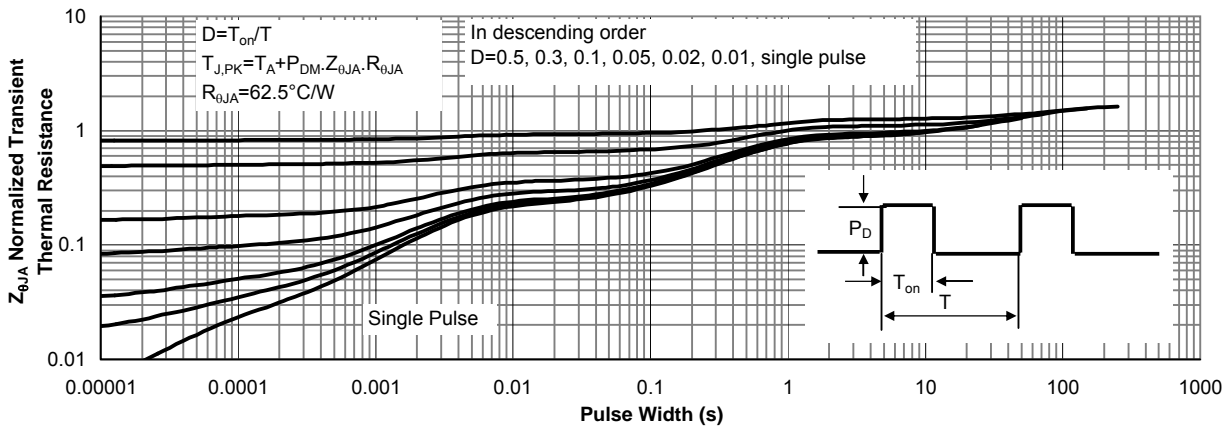


Figure 11: Normalized Maximum Transient Thermal Impedance

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: SCHOTTKY

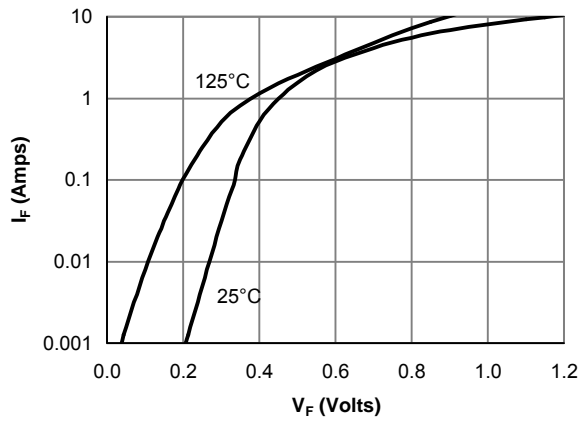


Figure 12: Schottky Forward Characteristics

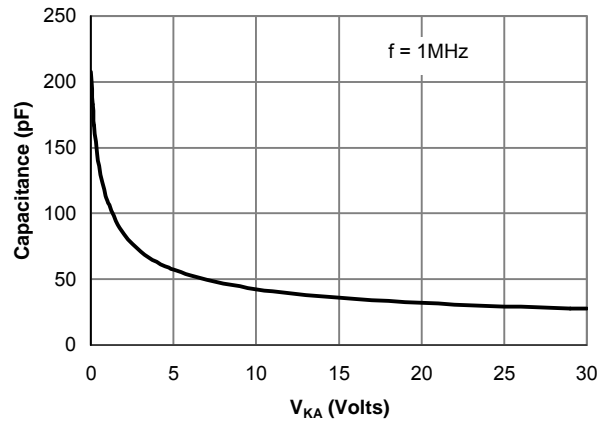


Figure 13: Schottky Capacitance Characteristics

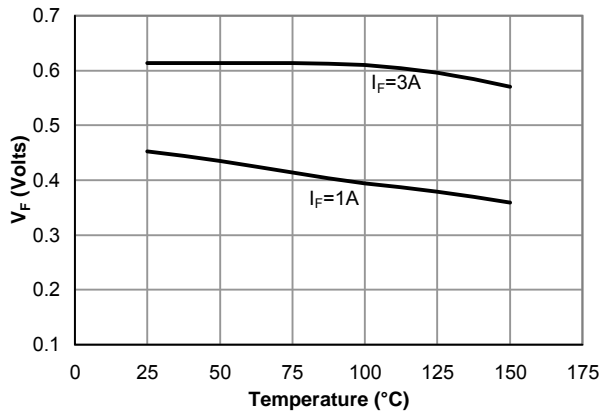


Figure 14: Schottky Forward Drop vs. Junction Temperature

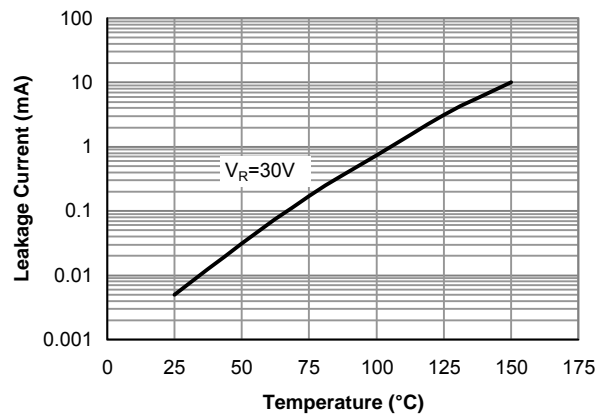


Figure 15: Schottky Leakage current vs. Junction Temperature

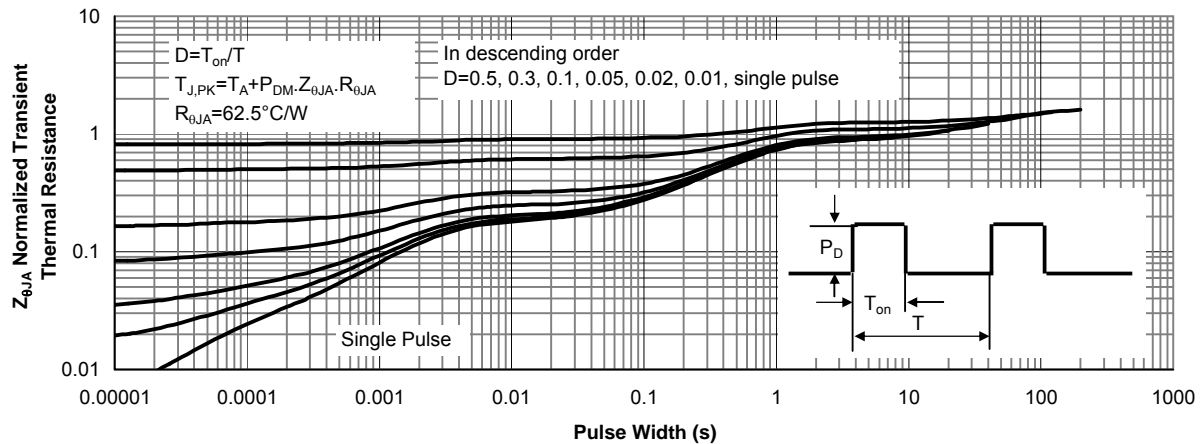


Figure 15: Schottky Normalized Maximum Transient Thermal Impedance